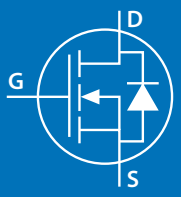
EPC2054 – Enhancement Mode Power Transistor

V_{DS}, 200 V
$R_{DS(on)}$, 43 mΩ
I_D, 3 A



EFFICIENT POWER CONVERSION

RoHS Halogen-Free

Revised June 11, 2021

Gallium Nitride's exceptionally high electron mobility and low temperature coefficient allows very low $R_{DS(on)}$, while its lateral device structure and majority carrier diode provide exceptionally low Q_G and zero Q_{RR}. The end result is a device that can handle tasks where very high switching frequency, and low on-time are beneficial as well as those where on-state losses dominate.

Questions: Ask a GaN Expert

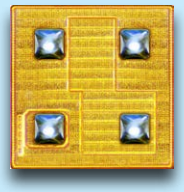
Maximum Ratings			
PARAMETER		**VALUE**	**UNIT**
V_{DS}	Drain-to-Source Voltage (Continuous)	200	V
I_D	Continuous (T_A = 25°C)	3	A
	Pulsed (25°C, T_{PULSE} = 300 µs)	32	
V_{GS}	Gate-to-Source Voltage	6	V
	Gate-to-Source Voltage	-4	
T_J	Operating Temperature	–40 to 150	°C
T_{STG}	Storage Temperature	–40 to 150	

Thermal Characteristics			
PARAMETER		**TYP**	**UNIT**
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	2.9	°C/W
$R_{\theta JB}$	Thermal Resistance, Junction-to-Board	14	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1)	83	

Note 1: $R_{\theta JA}$ is determined with the device mounted on one square inch of copper pad, single layer 2 oz copper on FR4 board.
See https://epc-co.com/epc/documents/product-training/Appnote_Thermal_Performance_of_eGaN_FETs.pdf for details

Static Characteristics (T_J = 25°C unless otherwise stated)						
PARAMETER		**TEST CONDITIONS**	**MIN**	**TYP**	**MAX**	**UNIT**
BV_{DSS}	Drain-to-Source Voltage	V_{GS} = 0 V, I_D = 0.12 mA	200			V
I_{DSS}	Drain-Source Leakage	V_{GS} = 0 V, V_{DS} = 160 V		0.001	0.1	mA
I_{GSS}	Gate-to-Source Forward Leakage	V_{GS} = 5 V		0.003	0.5	
	Gate-to-Source Forward Leakage#	V_{GS} = 5 V, T_J = 125°C		0.1	1	
	Gate-to-Source Reverse Leakage	V_{GS} = -4 V		0.001	0.1	
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D =1 mA	0.8	1.2	2.5	V
$R_{DS(on)}$	Drain-Source On Resistance	V_{GS} = 5 V, I_D = 1 A		32	43	mΩ
V_{SD}	Source-Drain Forward Voltage#	I_S = 0.5 A, V_{GS} = 0 V		1.5		V

Defined by design. Not subject to production test.



Die Size: 1.3 x 1.3 mm

EPC2054 eGaN® FETs are supplied only in passivated die form with solder bumps

Applications

- High Speed DC-DC conversion
- Wireless power transfer
- High frequency hard-switching and soft-switching circuits
- Lidar/time of flight (ToF)
- Automation
- Solar
- Class-D audio

Benefits

- Ultra high efficiency
- Ultra low $R_{DS(on)}$
- Ultra low Q_G
- Ultra small footprint

Scan QR code or click link below for more information including reliability reports, device models, demo boards!

https://l.ead.me/EPC2054

Dynamic Characteristics# (T_J = 25°C unless otherwise stated)						
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
C_{ISS}	Input Capacitance	V_{DS} = 100 V, V_{GS} = 0 V		358	573	pF
C_{RSS}	Reverse Transfer Capacitance			0.3		
C_{OSS}	Output Capacitance			89	134	
$C_{OSS(ER)}$	Effective Output Capacitance, Energy Related (Note 2)	V_{DS} = 0 to 100 V, V_{GS} = 0 V		120		
$C_{OSS(TR)}$	Effective Output Capacitance, Time Related (Note 3)			152		
R_G	Gate Resistance			0.8		Ω
Q_G	Total Gate Charge	V_{DS} = 100 V, V_{GS} = 5 V, I_D = 1 A		2.9	4.3	nC
Q_{GS}	Gate-to-Source Charge	V_{DS} = 100 V, I_D = 1 A		0.9		
Q_{GD}	Gate-to-Drain Charge			0.3		
$Q_{G(TH)}$	Gate Charge at Threshold			0.7		
Q_{OSS}	Output Charge	V_{DS} = 100 V, V_{GS} = 0 V		15	23	
Q_{RR}	Source-Drain Recovery Charge			0		

Defined by design. Not subject to production test.
All measurements were done with substrate connected to source.
Note 2: $C_{OSS(ER)}$ is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 to 50% BV_{DSS}.
Note 3: $C_{OSS(TR)}$ is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 50% BV_{DSS}.

Figure 1: Typical Output Characteristics 25°C

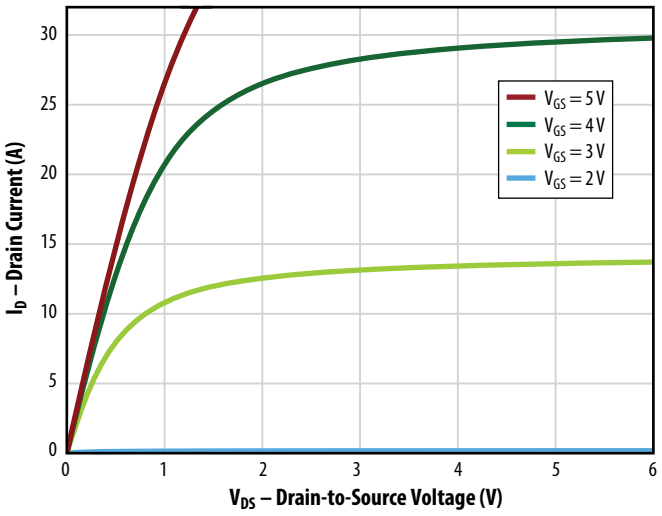


Figure 2: Typical Transfer Characteristics

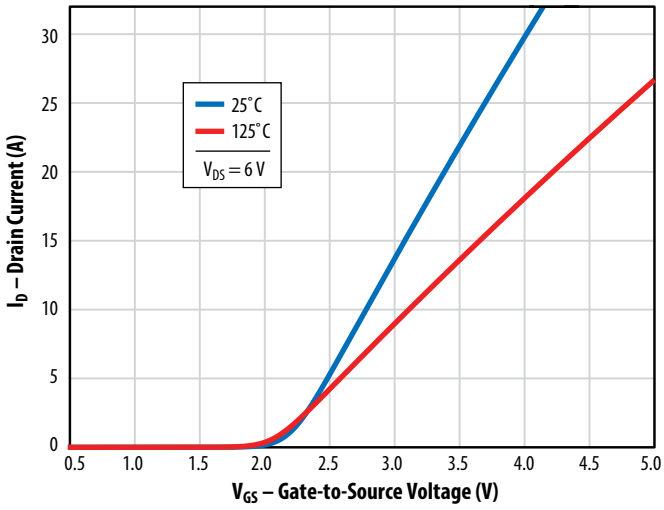


Figure 3: Typical $R_{DS(on)}$ vs. V_{GS} for Various Drain Currents

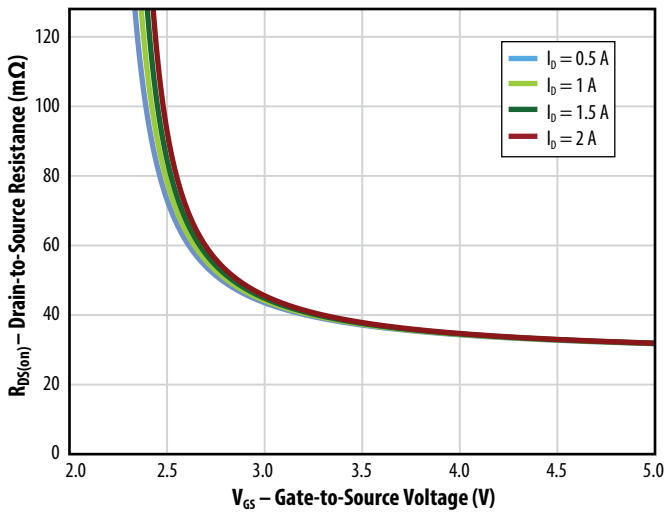


Figure 4: Typical $R_{DS(on)}$ vs. V_{GS} for Various Temperatures

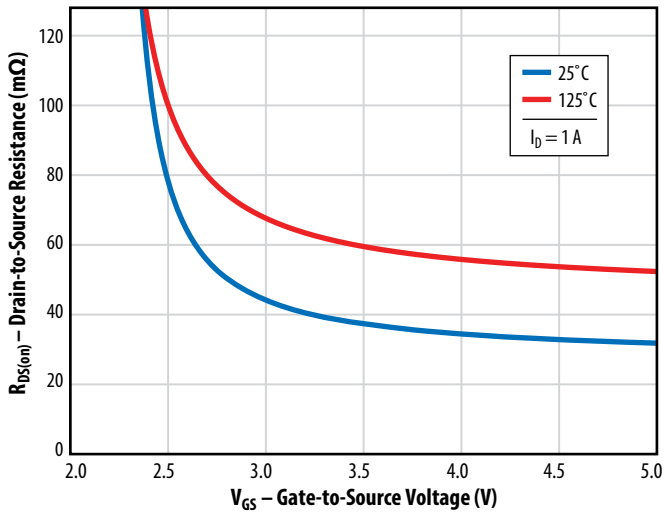


Figure 5a: Typical Capacitance (Linear Scale)

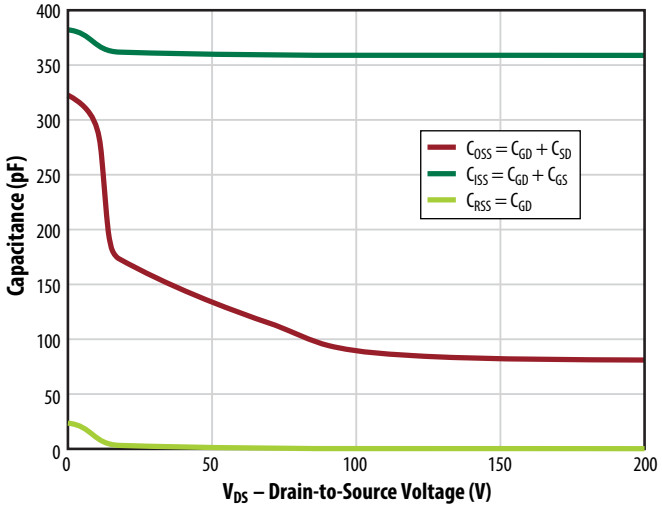


Figure 5b: Typical Capacitance (Log Scale)

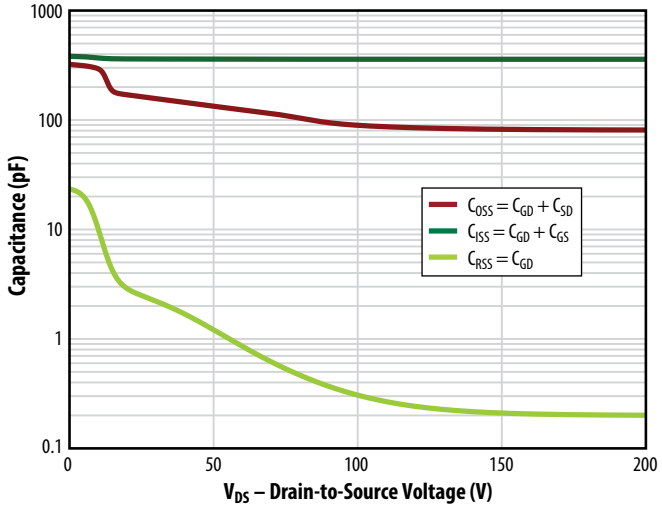


Figure 6: Typical Output Charge and C_{OSS} Stored Energy

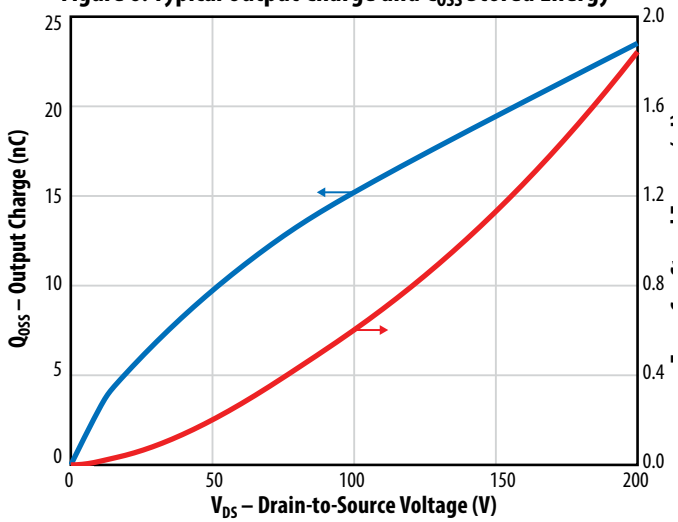


Figure 7: Typical Gate Charge

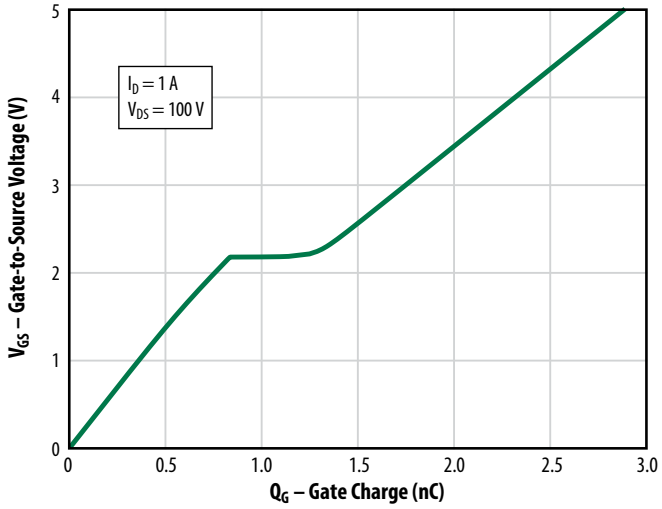


Figure 8: Typical Reverse Drain-Source Characteristics

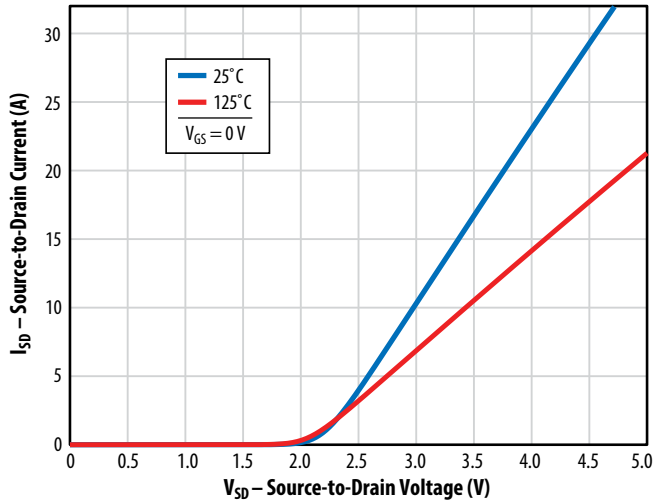
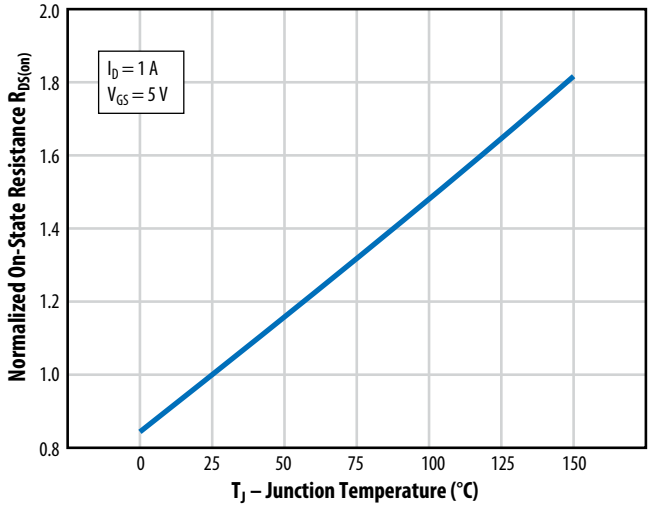


Figure 9: Typical Normalized On Resistance vs. Temperature



Note: Negative gate drive voltage increases the reverse drain-source voltage. EPC recommends 0 V for OFF.

All measurements were done with substrate shortened to source.

Figure 10: Typical Normalized Threshold Voltage vs. Temp.

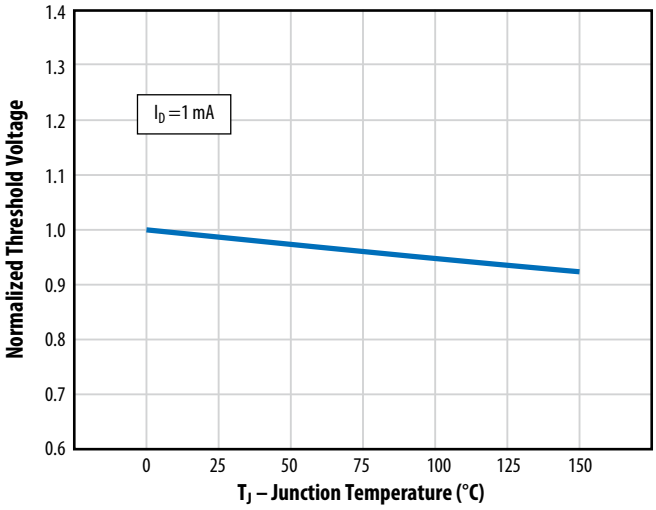
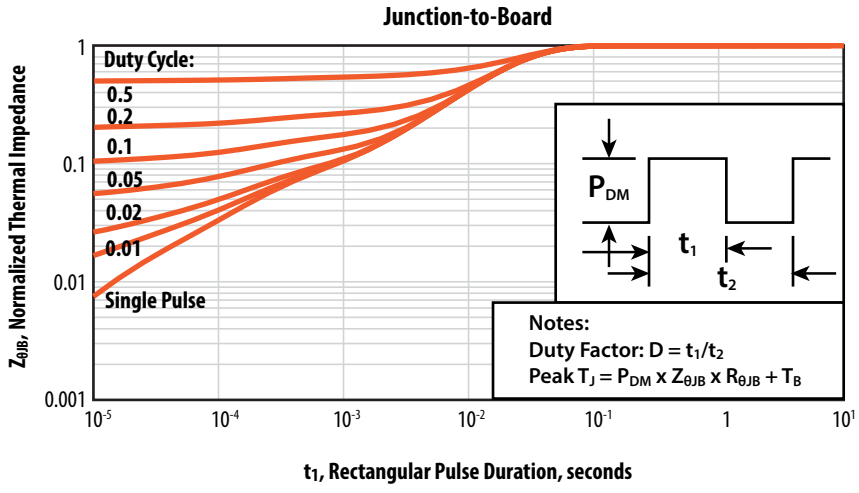


Figure 11: Typical Transient Thermal Response Curves



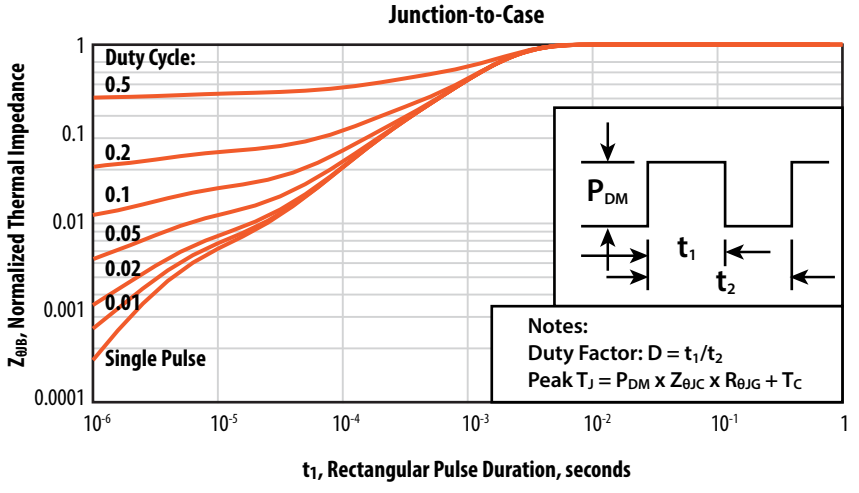
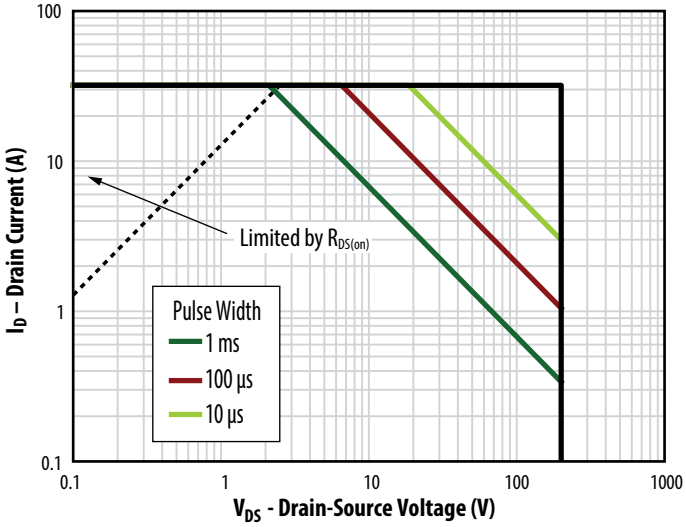
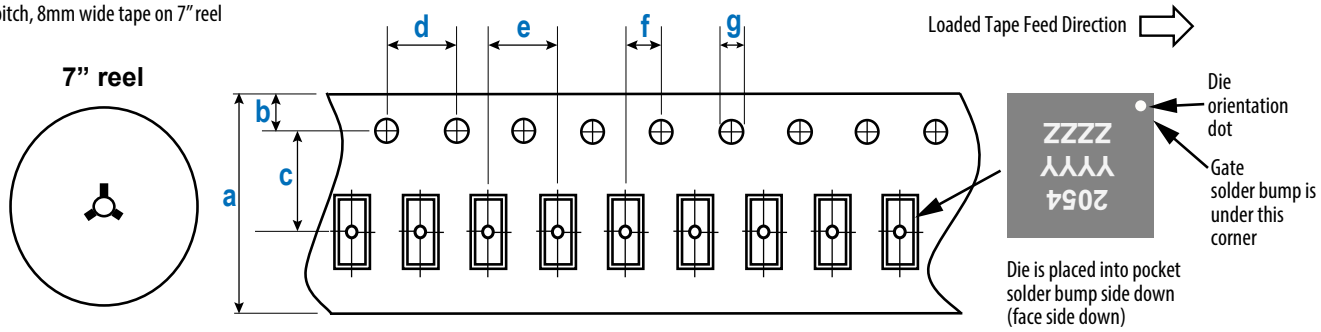


Figure 12: Safe Operating Area



TAPE AND REEL CONFIGURATION

4mm pitch, 8mm wide tape on 7" reel

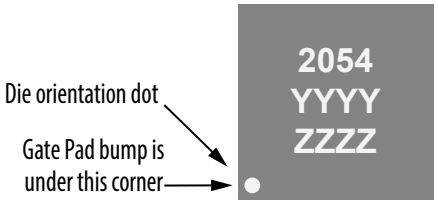


	Dimension (mm)		
EPC2054 (Note 1)	Target	MIN	MAX
a	8.00	7.90	8.30
b	1.75	1.65	1.85
c (Note 2)	3.50	3.45	3.55
d	4.00	3.90	4.10
e	4.00	3.90	4.10
f (Note 2)	2.00	1.95	2.05
g	1.50	1.50	1.60

Note 1: MSL 1 (moisture sensitivity level 1) classified according to IPC/JEDEC industry standard.

Note 2: Pocket position is relative to the sprocket hole measured as true position of the pocket, not the pocket hole.

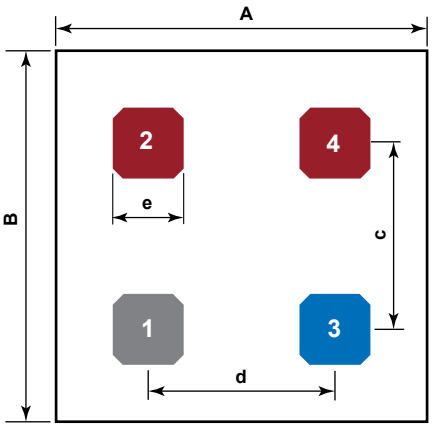
DIE MARKINGS



Part Number	Laser Markings		
	Part # Marking Line 1	Lot_Date Code Marking Line 2	Lot_Date Code Marking Line 3
EPC2054	2054	YYYY	ZZZZ

DIE OUTLINE

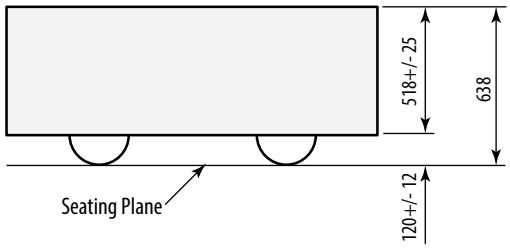
Solder Bump View



Pad 1 is Gate;
Pad 3 is Drain;
Pads 2, 4 are Source

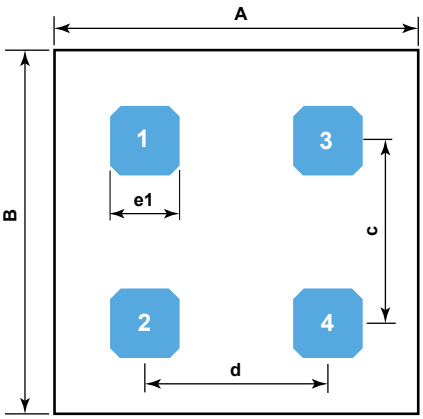
DIM	Micrometers		
	MIN	Nominal	MAX
A	1270	1300	1330
B	1270	1300	1330
c		650	
d		650	
e		250	

Side View



RECOMMENDED LAND PATTERN

(measurements in µm)



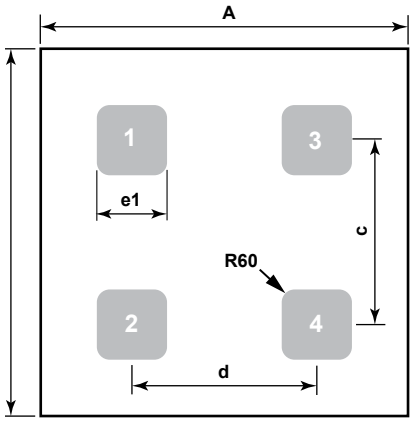
DIM	Micrometers
A	1300
B	1300
c	650
d	650
e1	230

The land pattern is solder mask defined.

Pad 1 is Gate;
Pad 3 is Drain;
Pads 2, 4 are Source

RECOMMENDED STENCIL DRAWING

(measurements in µm)



DIM	Micrometers
A	1300
B	1300
c	650
d	650
e1	230

Recommended stencil should be 4mil (100 µm) thick, must be laser cut, openings per drawing.
The corner has a radius of R60.
Intended for use with SAC305 Type 4 solder, reference 88.5% metals content.
Additional assembly resources available at https://epc-co.com/epc/design-support